

N-Channel 80V MOSFET

E080N8P7AH1

V_{DS} (V)	$R_{DS(on),max}$ (m Ω)	I_D (A)
80V	8.7 @ $V_{GS} = 10V$	81

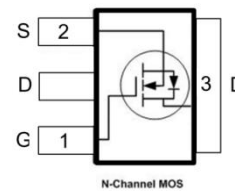
Features

- Low $R_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed
- 100% avalanche tested

Applications

- DC/DC conversion
- Power switch
- PD charger
- Moto driver

TO-220



Package And Ordering Information

Ordering code	Package	Marking
E080N8P7AH1	TO-220	E080N8P7AH1

Ordering Information

Package	Units/ Tube	Tubes/ Inner Box	Units/ Inner Box
TO-220	50	20	1000

Key Performance Parameters

Parameter	Value	Unit
VDS, min @ Tj(max)	80	V
ID, pulse	324	A
RDS(ON), max @ VGS=10V	8.7	mΩ
Qg	112	nC

Absolute Maximum Ratings at Tj=25°C Unless Otherwise Noted

Parameter		Symbol	Limit	Unit
Drain-source voltage		V _{DS}	80	V
Gate-source voltage		V _{GS}	±20	
Continuous drain current	T _C =25°C	I _D	81	A
	T _C =100°C		51	
Pulsed drain current		I _{D,pulse}	324	
Avalanche energy, single pulse		E _{AS}	361	mJ
Power dissipation	T _C =25°C	P _D	125	W
	T _C =100°C		50	
Operating junction and storage temperature range		T _J , T _{stg}	-55 To 150	°C

Thermal Characteristics

Parameter		Symbol	Max.	Unit
Thermal resistance, junction-to-case	Steady state	R _{θJC}	1	°C/W
Thermal resistance, junction-to-ambient	Steady state	R _{θJA}	-	

Electrical Characteristics at Tj=25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Static						
Drain to source breakdown voltage	V _{(BR)DSS}	80			V	V _{GS} = 0, I _D = 250 μA
Gate-source threshold voltage	V _{GS(th)}	2	2.85	4	V	V _{DS} = V _{GS} , I _D = 250 μA
Gate-body leakage	I _{GSS}			±100	nA	V _{DS} = 0 V, V _{GS} = ±20 V
Zero gate voltage drain current	I _{DSS}			1	μA	V _{DS} = 80 V, V _{GS} = 0 V
Drain-source on-resistance	R _{DS(on)}		7.6	8.7	mΩ	V _{GS} = 10 V, I _D = 40 A
Forward transconductance	g _{fs}		36		S	V _{DS} = 10 V, I _D = 40 A
Gate resistance	R _g		0.5		Ω	f=1MHz

Gate Charge						
Total gate charge	Qg		112		nC	V _{DS} = 40 V, I _D = 20 A, V _{GS} = 10 V
Gate-source charge	Qgs		15			
Gate-drain charge	Qgd		45			
Dynamic						
Turn-on delay time	t _{d(on)}		30		ns	V _{DS} = 40 V, V _{GS} = 10 V, R _L = 2 Ω, R _{GEN} = 6 Ω
Rise time	t _r		18			
Turn-off delay time	t _{d(off)}		65			
Fall time	t _f		30			
Input capacitance	C _{iss}		4450		pF	V _{DS} =40 V, V _{GS} = 0 V, f = 1.0MHz
Output capacitance	C _{oss}		210			
Reverse transfer capacitance	C _{rss}		180			
Body Diode						
Diode forward voltage	V _{SD}			1.2	V	V _{GS} = 0 V, I _F = 20 A
Reverse recovery time	t _{rr}		7		ns	I _S =20 A, di/dt = 100 A/μs
Reverse recovery charge	Q _{rr}		40		nC	

Electrical Characteristics Diagrams

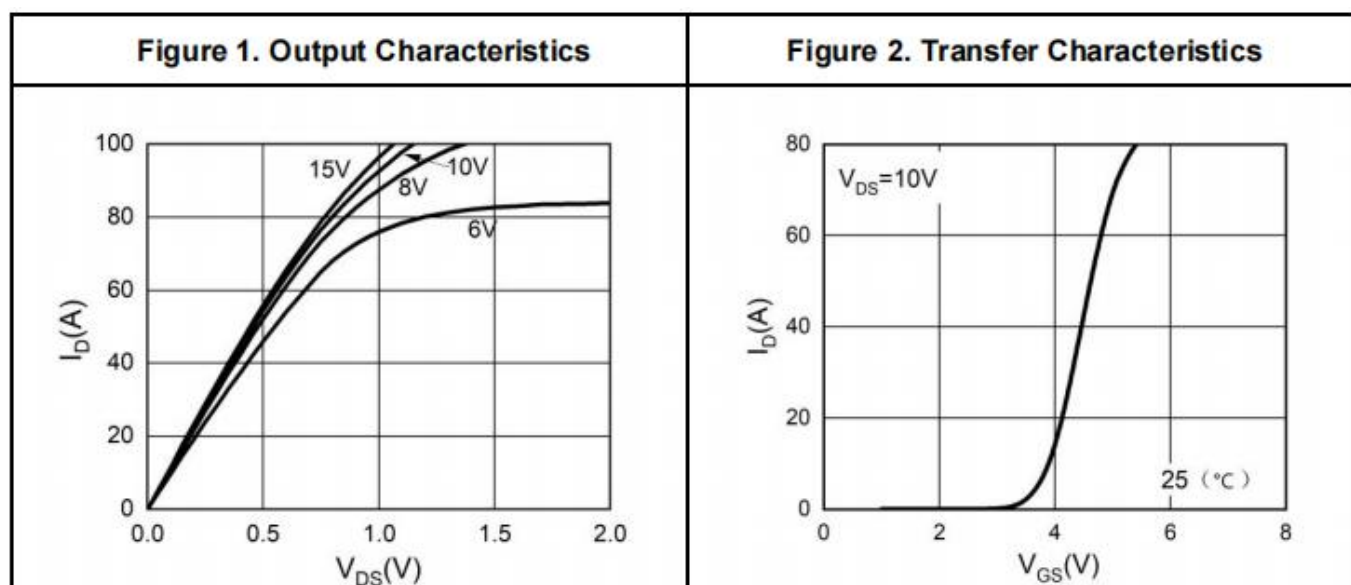


Figure 3. Power Dissipation

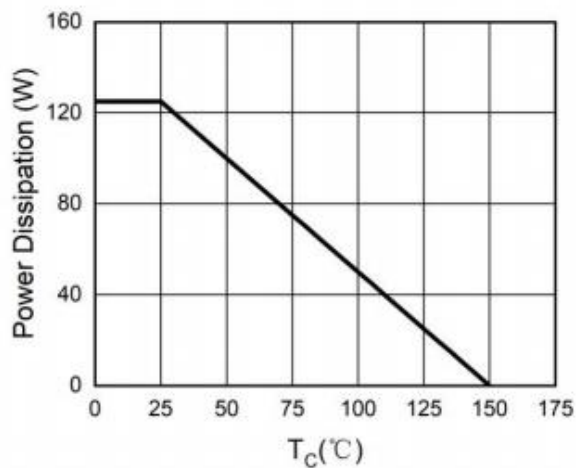


Figure 4. Drain Current

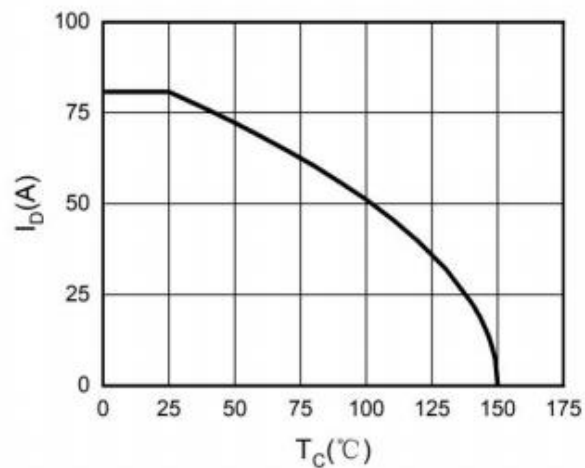


Figure 5. BV_{DSS} vs Junction Temperature

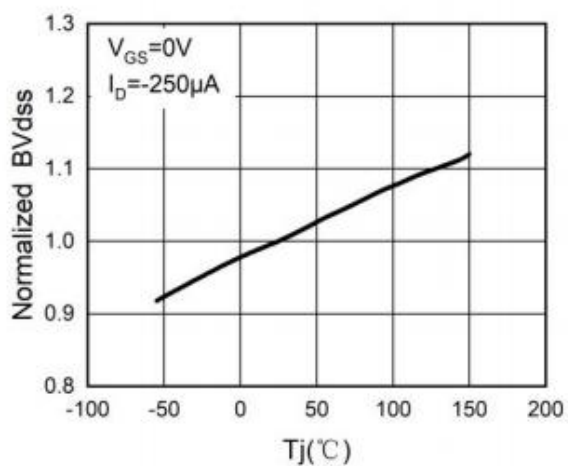


Figure 6. $R_{DS(ON)}$ vs Junction Temperature

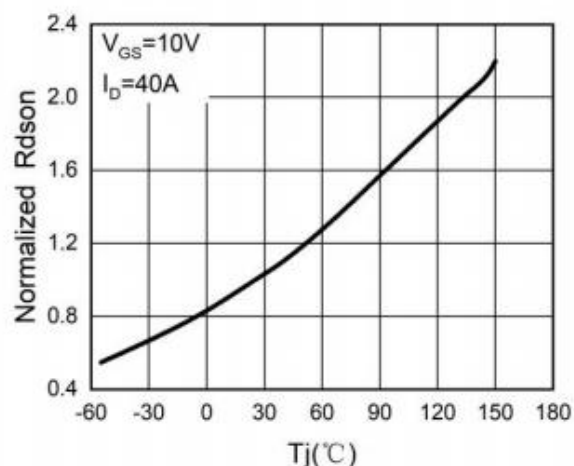
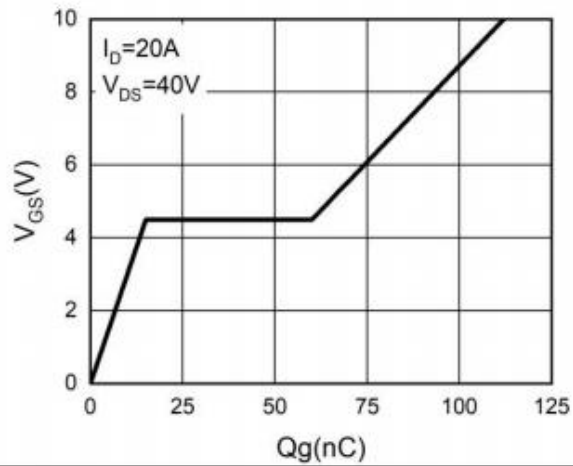
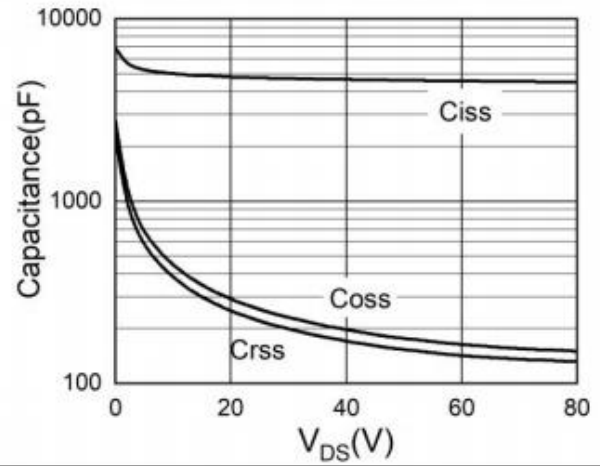
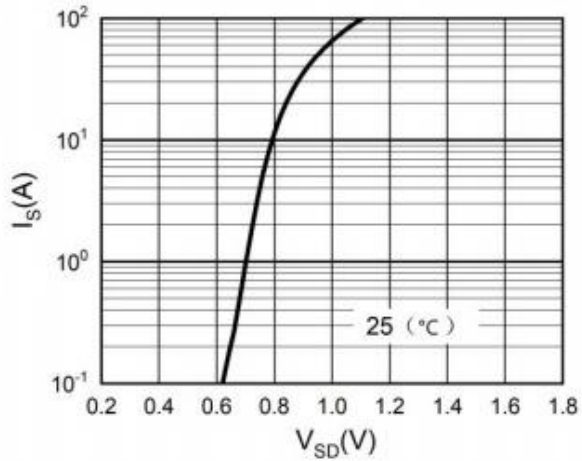
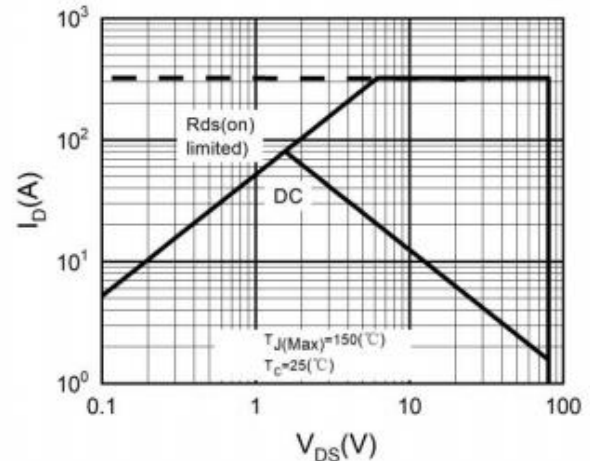
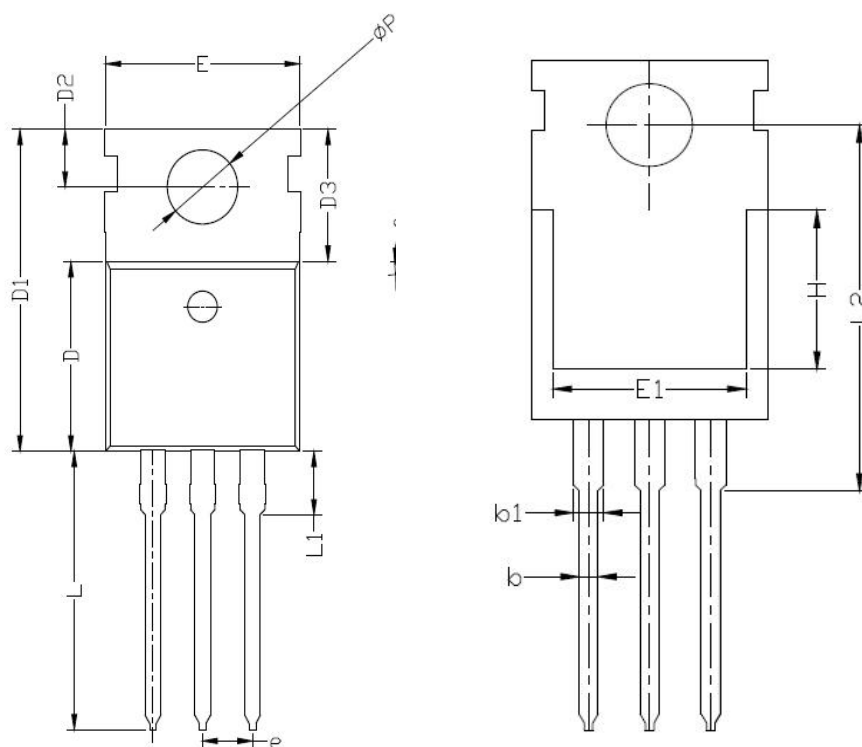


Figure 7. Gate Charge Waveforms

Figure 8. Capacitance

Figure 9. Body-Diode Characteristics

Figure 10. Maximum Safe Operating Area


Package Outline Dimensions



Symbols	Millimeters		
	MIN.	NOM.	MAX.
A	4,27	4,57	4,87
A1	1,15	1,30	1,45
A2	2,20	2,40	2,60
C	0,40	0,50	0,65
L1	2,80	3,10	3,40
L	13,20	13,50	13,70
L2	15,50	15,90	16,30
D	9,00	9,20	9,40
D1	15,10	15,60	16,10
D2	2,60	2,80	3,00
D3	6,20	6,40	6,60
e	2,54 BSC.		
H	6,70	6,90	7,10
E	9,70	9,90	10,10
E1	7,80	8,00	8,20
ØP	3,40	3,60	3,80
b	0,70	0,80	0,90
b1	1,17	1,27	1,37
θ	4°	7°	10°
0,1	0°	3°	6°

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